SYSTEM AND METHOD FOR INTEGRATED OXIDE REMOVAL AND PROCESSING OF A SEMICONDUCTOR WAFER

ABSTRACT OF THE DISCLOSURE

An integrated oxide removal and processing system (10) includes a process module (30) that may intentionally add at least one film layer to a single semiconductor wafer (32). The integrated oxide removal and processing system (10) also includes a transfer chamber module (20) used to align the semiconductor wafer (32) for the process module (30). The transfer chamber module (20) may expose the semiconductor wafer (32) to a vaporous solution that is inert with respect to the semiconductor wafer (32) and operable to remove an oxide layer (110) therefrom. More specifically, the semiconductor wafer (32) includes silicon. In a further embodiment, the vaporous solution includes HF. In yet a further embodiment, the vaporous solution includes .049% to 49% HF.